

Features:

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses
- Short turn-off time
- Hermetic metal cases with ceramic insulators

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters
- AC motor speed control
- General power switching applications

$I_{T(AV)}$ **1430A**
 V_{DRM}/V_{RRM} **800~1200V**
 t_q **10~20μs**
 I_{TSM} **15 kA**



| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | T _j (°C) | VALUE | | | UNIT |
|--------------------------------------|--|--|----------------------|-------|------|-------|----------------------------------|
| | | | | Min | Type | Max | |
| I _{T(AV)} | Mean on-state current | 180° half sine wave 50Hz Double side cooled, | T _C =55°C | | | 1430 | A |
| | | | T _C =85°C | | | 960 | |
| V _{DRM} V _{RRM} | Repetitive peak off-state voltage Repetitive peak reverse voltage | V _{DRM} &V _{RRM} ,tp=10ms V _{DSM} &V _{RSM} = V _{DRM} &V _{RRM} +100V | 125 | 800 | | 1200 | V |
| I _{DRM} I _{RRM} | Repetitive peak off state current Repetitive peak reverse current | V _D = V _{DRM} V _R = V _{RRM} | 125 | | | 80 | mA |
| I _{TSM} | Surge on-state current | 10ms half sine wave | 125 | | | 15 | kA |
| I ² t | I ² T for fusing coordination | V _R =0.6V _{RRM} | | | | 1125 | A ² s*10 ³ |
| V _{TO} | Threshold voltage | | 125 | | | 1.32 | V |
| r _T | On-state slop resistance | | | | | 0.32 | mΩ |
| V _{TM} | Peak on-state voltage | I _{TM} =2000A, F=24kN | 125 | | | 2.02 | V |
| dv/dt | Critical rate of rise of off-state voltage | V _{DM} =0.67V _{DRM} | 125 | | | 200 | V/μs |
| di/dt | Critical rate of rise of on-state current | V _{DM} = 67%V _{DRM} ,to2000A Gate pulse t _r ≤0.5μs I _{GM} =1.5A | 125 | | | 1500 | A/μs |
| Q _{rr} | Recovery charge | I _{TM} =2000A, tp=2000μs, di/dt=-60A/μs, V _R =50V | 125 | | 77 | 100 | μC |
| t _q | Circuit commutated turn-off time | I _{TM} =1200A, tp=1000μs, V _R =50V dv/dt=30V/μs ,di/dt=-20A/μs | 125 | 10 | | 20 | μs |
| I _{GT} | Gate trigger current | V _A =12V, I _A =1A | 25 | 30 | | 300 | mA |
| V _{GT} | Gate trigger voltage | | | 0.8 | | 3.0 | V |
| I _H | Holding current | | | 20 | | 400 | mA |
| V _{GD} | Non-trigger gate voltage | V _{DM} =67%V _{DRM} | 125 | 0.3 | | | V |
| R _{th(j-c)} | Thermal resistance Junction to case | At 180° sine double side cooled Clamping force 24kN | | | | 0.020 | °C /W |
| R _{th(c-h)} | Thermal resistance case to heat sink | | | | | 0.005 | |
| F _m | Mounting force | | | 19 | | 26 | kN |
| T _{stg} | Stored temperature | | | -40 | | 140 | °C |
| W _i | Weight | | | | 440 | | g |
| Outline | KT50cT | | | | | | |

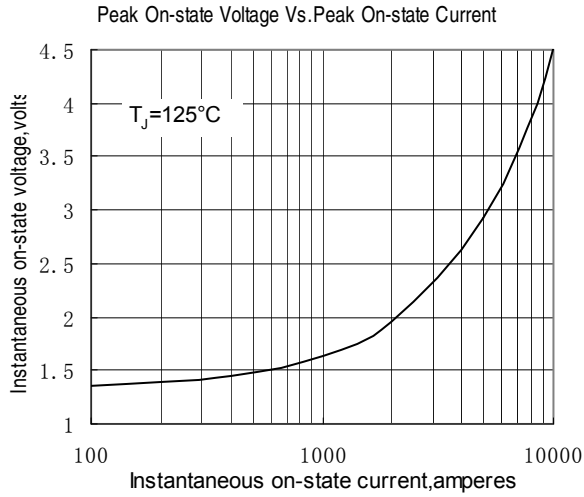


Fig.1

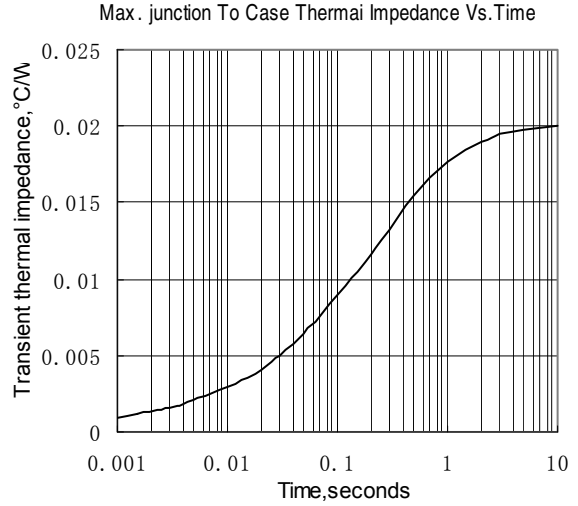


Fig.2

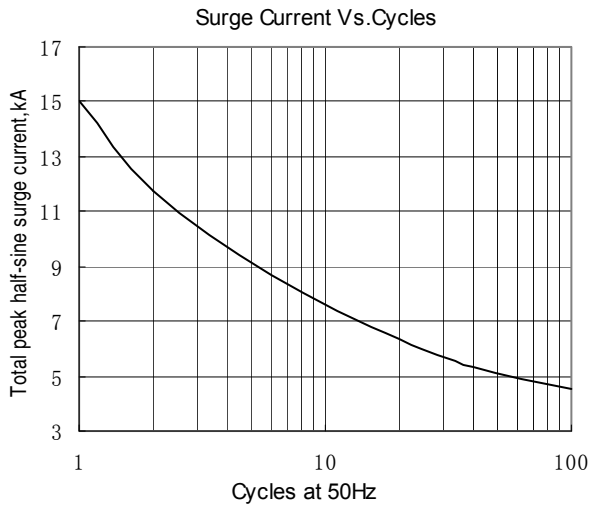


Fig.3

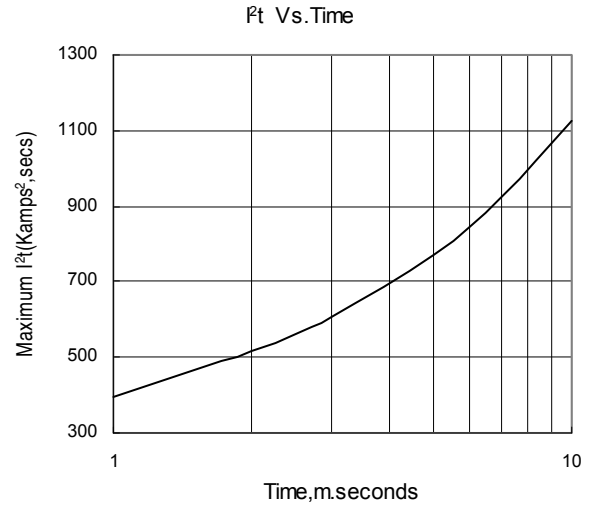


Fig.4

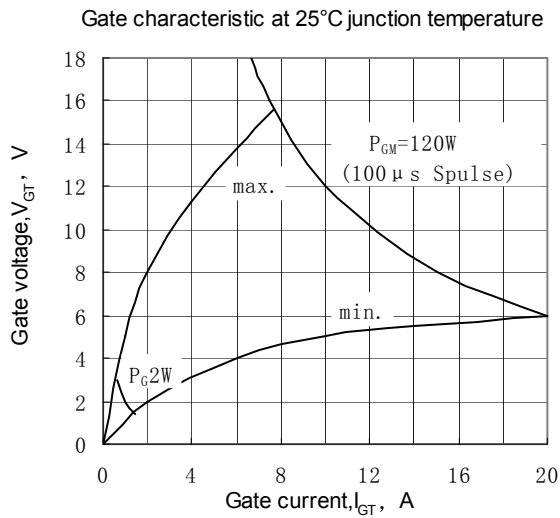


Fig.5

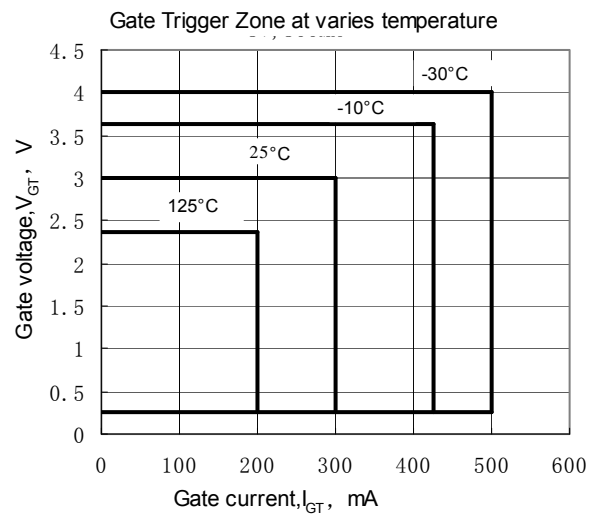


Fig.6

Outline:

